

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S29	6	"6524935"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 13:06
S30	862	("SiGe" 'sige' silicon near3 geranium) with (strained relaxed)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 14:23
S31	632	S30 and (implant\$3 nitridation nitrify nitrification inject\$3 silicide silicidation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:02
S32	632	S30 and (implant\$3 nitridation nitrify nitrification inject\$3 silicide silicidation oxynitridation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:03
S33	175	S32 and ("SiGe" 'sige' silicon near3 geranium) with (crystalline ((mono single) near3 (crystal crystalline)))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:07
S34	166	S33 and ("SiGe" 'sige' silicon near3 geranium) with ('soi' insulat\$3 substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:08
S35	166	S34 and (nitride silicon oxynitride nitrogen germanium metal metal\$4 heat\$3 anneal\$3 oxide)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 10:16
S37	1	S35 and vacan\$3	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 09:12
S38	95	S35 and \$4nitrid\$7	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 18:08
S39	10	"6455398"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/21 18:08

S40	1	10/765999	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 13:07
S41	1076	("SiGe" "GeSi" 'sige' 'gesi' silicon near3 geranium) with (strained strain relaxed relaxation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 14:31
S42	1076	S41 and ("SiGe" "GeSi" 'sige' 'gesi' silicon near3 geranium strained strain relaxed relaxation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 14:32
S43	37	S42 and strain\$3 near3 inducing	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/04/22 14:32

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	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	-
20	r	r	US 6849883	2005020	15	Strained SOI MOSFET d	257/192	257/190;	Okihara; Masao	F	r	r	r	r	r
21	r	r	US 6831292	2004121	13	Semiconductor structures	257/19	257/18	Currie; Matthew et	F	r	r	r	r	r
22	r	r	US 6830976	2004121	25	Relaxed silicon germani	438/287	438/300;	Fitzgerald; Eugene	F	r	r	r	r	r
23	r	r	US 6815738	2004110	10	Multiple gate MOSFET s	257/256	257/213;	Rim; Kern	F	r	r	r	r	r
24	r	r	US 6815279	2004110	35	Manufacturing method of	438/199	257/369	Yagishita; Atsushi e	F	r	r	r	r	r
25	r	r	US 6787852	2004090	7	Semiconductor-on-insula	257/347	257/348;	Yu; Bin et al.	F	r	r	r	r	r
26	r	r	US 6787793	2004090	10	Strained Si device with fir	257/19	257/15;	Yoshida; Akira	F	r	r	r	r	r
27	r	r	US 6770134	2004080	27	Method for fabricating w	117/89	117/103;	Maydan; Dan et al.	F	r	r	r	r	r
28	r	r	US 6765227	2004072	8	Semiconductor-on-insula	257/19	257/192;	Yu; Bin et al.	F	r	r	r	r	r
29	r	r	US 6750130	2004061	13	Heterointegration of mate	438/607	257/E21.5	Fitzgerald; Eugene	F	r	r	r	r	r
30	r	r	US 6737670	2004051	18	Semiconductor substrate	257/19	257/E21.1	Cheng; Zhi-Yuan et	F	r	r	r	r	r
31	r	r	US 6730551	2004050	11	Formation of planar strai	438/191	257/E21.6	Lee; Minjoo L. et al	F	r	r	r	r	r
32	r	r	US 6724008	2004042	28	Relaxed silicon germani	257/19	257/190;	Fitzgerald; Eugene	F	r	r	r	r	r
33	r	r	US 6723661	2004042	28	Relaxed silicon germani	438/763	257/E21.1	Fitzgerald; Eugene	F	r	r	r	r	r
34	r	r	US 6713326	2004033	14	Process for producing se	438/149	257/E21.1	Cheng; Zhi-Yuan et	F	r	r	r	r	r
35	r	r	US 6703688	2004030	29	Relaxed silicon germani	257/616	257/190;	Fitzgerald; Eugene	F	r	r	r	r	r
36	r	r	US 6703144	2004030	16	Heterointegration of mate	428/641	117/953;	Fitzgerald; Eugene	F	r	r	r	r	r
37	r	r	US 6689211	2004021	28	Etch stop layer system	117/94	117/915;	Wu; Kenneth C. et	F	r	r	r	r	r
38	r	r	US 6680495	2004012	17	Silicon wafer with embed	257/183	257/184	Fitzgerald; Eugene	F	r	r	r	r	r

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	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	
39	<input type="checkbox"/>	US 6677655	2004011	16	Silicon wafer with embed	257/432	257/186;		Fitzgerald; Eugene	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
40	<input type="checkbox"/>	US 6649480	2003111	24	Method of fabricating C	438/285	257/E21.6		Fitzgerald; Eugene	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
41	<input type="checkbox"/>	US 6642536	2003110	11	Hybrid silicon on insulat	257/19	257/20;		Xiang; Qi et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
42	<input type="checkbox"/>	US 6633066	2003101	31	CMOS integrated circuit	257/347	257/348;		Bae; Geun-jong et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
43	<input type="checkbox"/>	US 6607948	2003081	18	Method of manufacturing	438/151	438/938		Sugiyama; Naoharu	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
44	<input type="checkbox"/>	US 6603156	2003080	6	Strained silicon on insula	257/190	257/347;		Rim; Kern	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
45	<input type="checkbox"/>	US 6602613	2003080	14	Heterointegration of mate	428/641	117/953;		Fitzgerald; Eugene	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
46	<input type="checkbox"/>	US 6597016	2003072	26	Semiconductor device an	257/77	257/289;		Yuki; Koichiro et al	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
47	<input type="checkbox"/>	US 6593641	2003071	26	Relaxed silicon germaniu	257/616	257/18;		Fitzgerald; Eugene	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
48	<input type="checkbox"/>	US 6573126	2003060	13	Process for producing se	438/149	257/E21.5		Cheng; Zhi-Yuan et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
49	<input type="checkbox"/>	US 6555839	2003042	20	Buried channel strained s	257/18	257/19;		Fitzgerald; Eugene	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
50	<input type="checkbox"/>	US 6521041	2003021	20	Etch stop layer system	117/94	117/915;		Wu; Kenneth C. et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
51	<input type="checkbox"/>	US 6495402	2002121	8	Semiconductor-on-insula	438/149	257/E21.4		Yu; Bin et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
52	<input type="checkbox"/>	US 6455871	2002092	10	SiGe MODFET with a m	257/12	257/189;		Shim; Kyu Hwan et	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
53	<input type="checkbox"/>	US 6410371	2002062	7	Method of fabrication of	438/151	257/E21.4		Yu; Bin et al.	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
54	<input type="checkbox"/>	US 6380590	2002043	7	SOI chip having multiple	257/350	257/289;		Yu; Bin	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
55	<input type="checkbox"/>	US 6350993	2002022	22	High speed composite p-c	257/19	257/18;		Chu; Jack Oon et al	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
56	<input type="checkbox"/>	US 6326667	2001120	13	Semiconductor devices a	257/347	257/18;		Sugiyama; Naoharu	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
57	<input type="checkbox"/>	US 6310367	2001103	32	MOS transistor having a t	257/190	257/19		Yagishita; Atsushi e	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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